



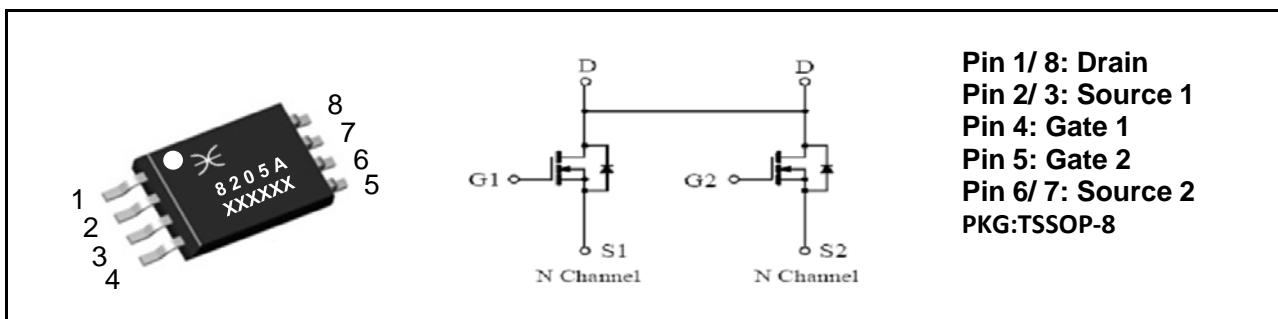
Dual N-Channel High Density Trench MOSFET (20V, 6A)

**PRODUCT SUMMARY**

$V_{DSS}$	$I_D$	$R_{DS(on)}$ (mΩ) Typ.
20V	6.0A	19 @ $V_{GS} = 4.5V$ , $I_D=6A$
		20@ $V_{GS} = 4.0V$ , $I_D=6A$
		25@ $V_{GS} = 2.5V$ , $I_D=5.2A$

**Features**

- Advanced Trench Process Technology
- High Density Cell Design for Ultra Low On-Resistance
- Surface mount Package
- Lead (Pb) -free and halogen-free



**Absolute Maximum Ratings** ( $T_A=25^\circ C$ , unless otherwise noted)

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Drain Current (Continuous)	6	A
$I_{DM}$	Drain Current (Pulsed) <sup>a</sup>	20	A
$P_D$	Total Power Dissipation @ $T_A=25^\circ C$	2	W
$I_S$	Maximum Diode Forward Current	1.7	A
$T_j, T_{stg}$	Operating Junction and Storage Temperature Range	-55 to +150	°C
$R_{QJA}$	Thermal Resistance Junction to Ambient (PCB mounted) <sup>b</sup>	62	°C/W

a: Repetitive Rating: Pulse width limited by the maximum junction temperature.

b: 1-in<sup>2</sup> 2oz Cu PCB board



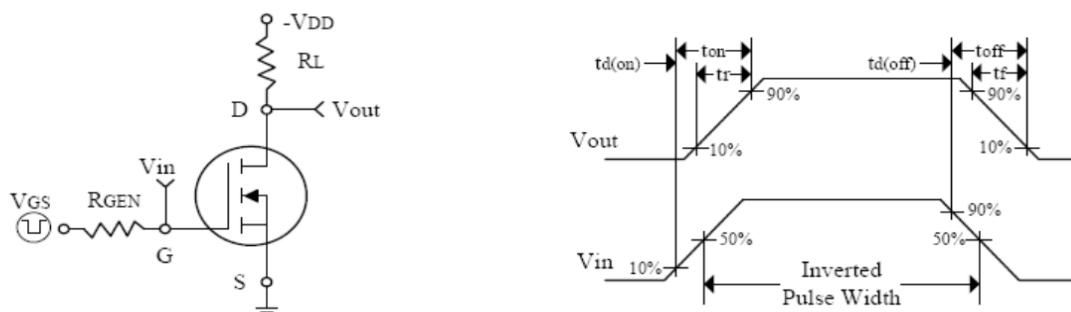
# Eternal Semiconductor Inc.

## ET8205A

**Electrical Characteristics** ( $T_A=25^\circ\text{C}$ , unless otherwise noted)

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
<b>• Off Characteristics</b>						
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	20	-	-	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}}=20\text{V}$ , $V_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
$I_{\text{GSS}}$	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 12\text{V}$ , $V_{\text{DS}}=0\text{V}$	-	-	$\pm 10$	$\mu\text{A}$
<b>• On Characteristics</b>						
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$ , $I_D=250\mu\text{A}$	0.5	0.65	1.0	V
$R_{\text{DS(on)}}$	Drain-Source On-State Resistance	$V_{\text{GS}}=4.5\text{V}$ , $I_D=6\text{A}$	-	19	24	$\text{m}\Omega$
		$V_{\text{GS}}=3\text{V}$ , $I_D=5.2\text{A}$	-	20	27	
		$V_{\text{GS}}=2.5\text{V}$ , $I_D=5.2\text{A}$	-	25	28	
<b>• Dynamic Characteristics</b>						
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}}=6\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	-	559	-	PF
$C_{\text{oss}}$	Output Capacitance		-	148	-	
$C_{\text{rss}}$	Reverse Transfer Capacitance		-	127	-	
<b>• Switching Characteristics</b>						
$Q_g$	Total Gate Charge	$V_{\text{DS}}=10\text{V}$ , $I_D=6\text{A}$ , $V_{\text{GS}}=4.5\text{V}$	-	5	-	nC
$Q_{\text{gs}}$	Gate-Source Charge		-	0.9	-	
$Q_{\text{gd}}$	Gate-Drain Charge		-	1.4	-	
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DD}}=10\text{V}$ , $R_L=1.2\Omega$ , $I_D=1\text{A}$ , $\text{VGEN}=10\text{V}$ , $\text{RG}=6\Omega$	-	10.2	-	nS
$t_r$	Turn-on Rise Time		-	7	-	
$t_{\text{d(off)}}$	Turn-off Delay Time		-	33	-	
$t_f$	Turn-off Fall Time		-	6.8	-	
<b>• Drain-Source Diode Characteristics</b>						
$V_{\text{SD}}$	Drain-Source Diode Forward Voltage	$V_{\text{GS}}=0\text{V}$ , $I_S=1.7\text{A}$	-	-	1.2	V

Note: Pulse Test: Pulse Width  $\leq 300\text{us}$ , Duty Cycle  $\leq 2\%$



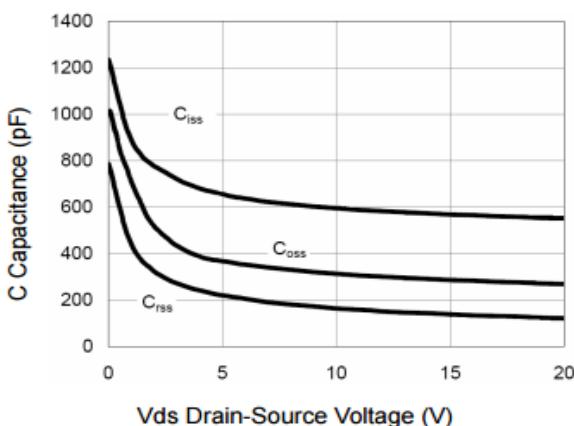
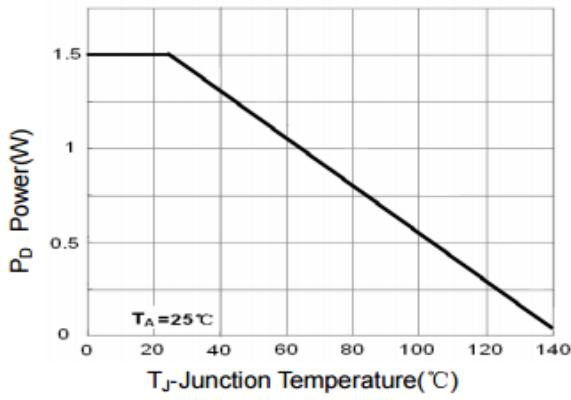
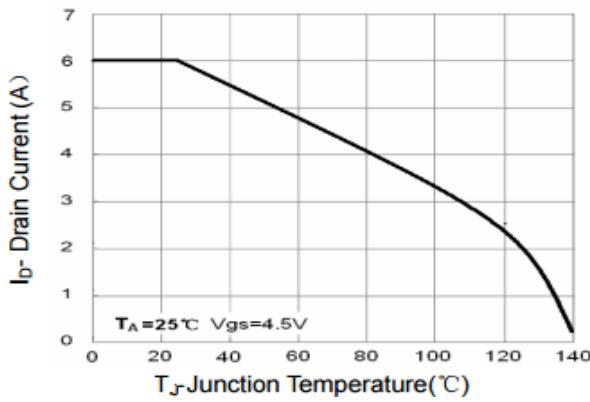
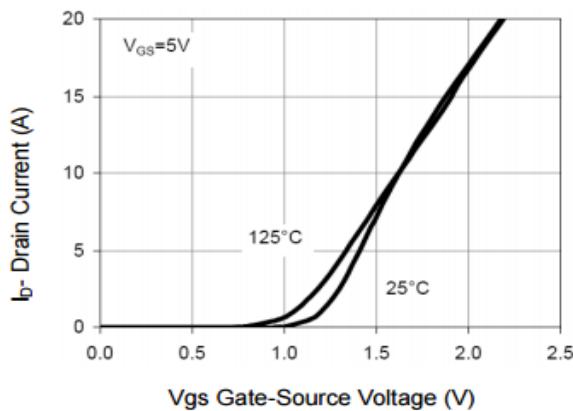
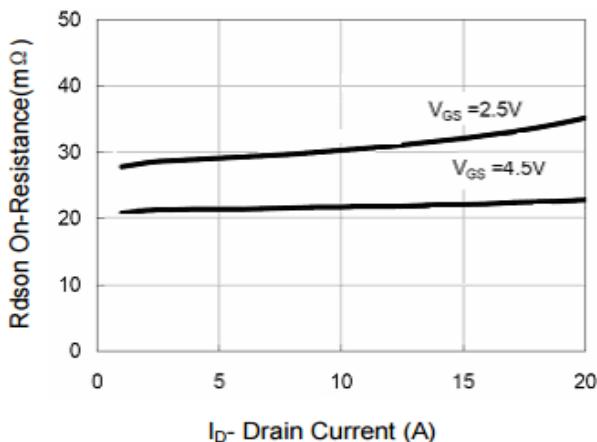
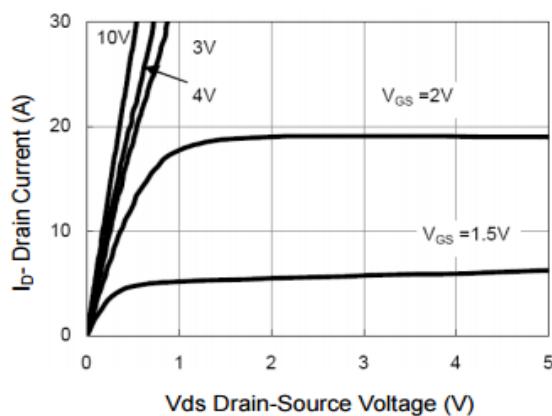
Switching Test Circuit and Switching Waveforms

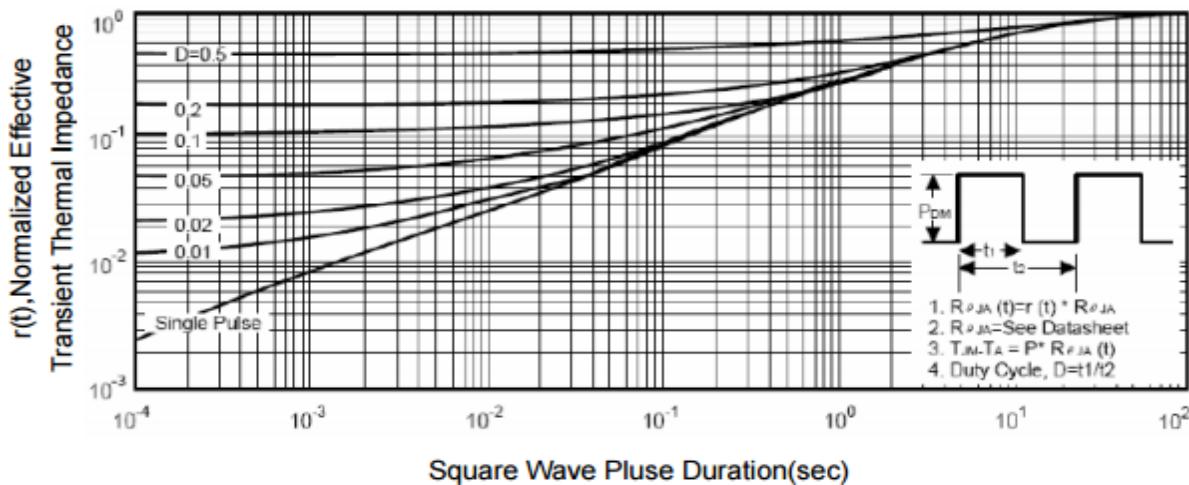
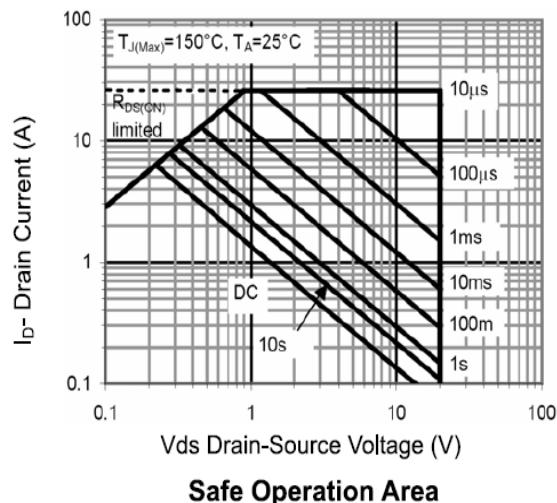
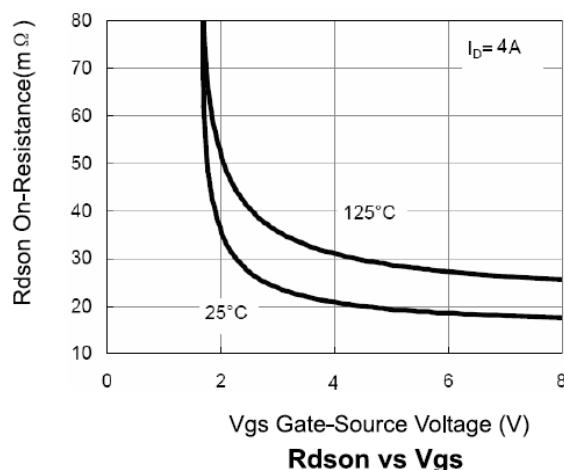
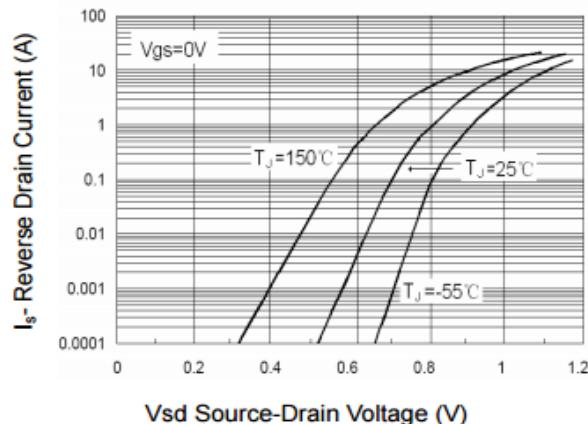
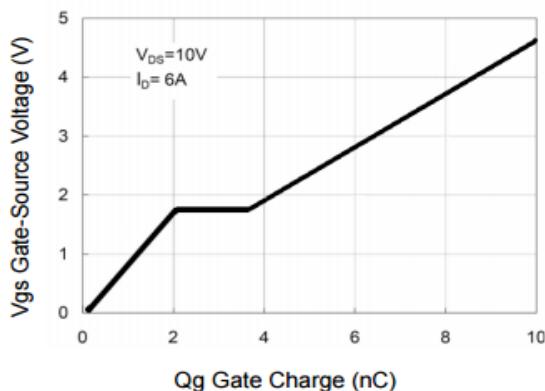


# Eternal Semiconductor Inc.

## ET8205A

Typical Characteristics Curves (Ta=25°C, unless otherwise note)



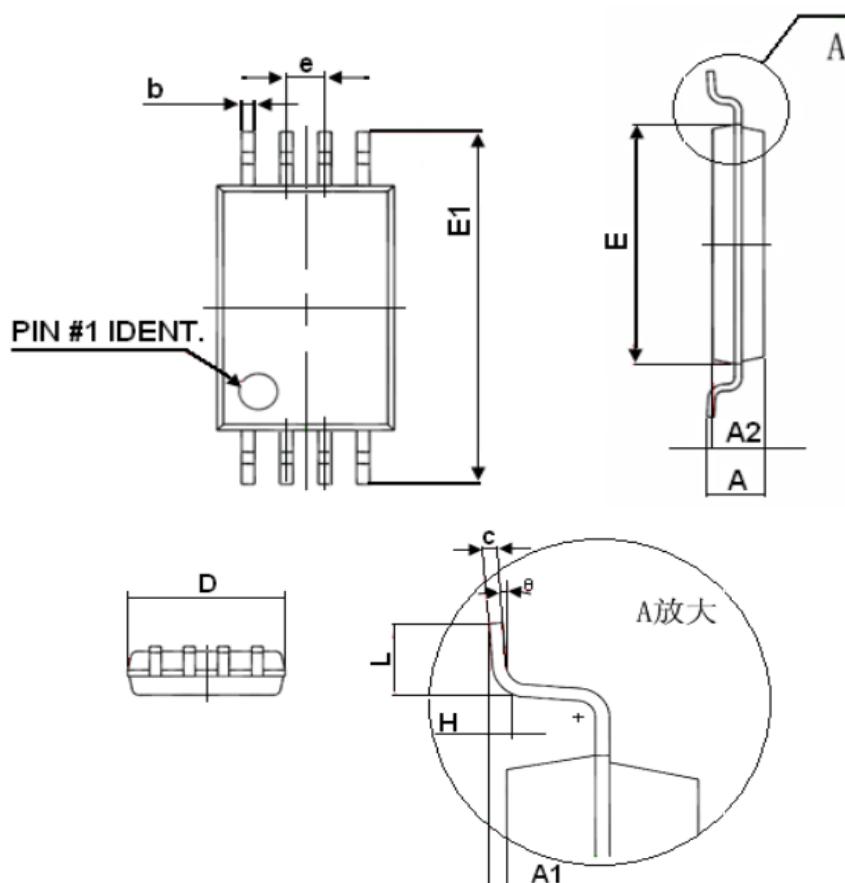




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## ET8205A

### TSSOP8 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters	
	Min	Max
D	2.900	3.100
E	4.300	4.500
b	0.190	0.300
c	0.090	0.200
E1	6.250	6.550
A		1.100
A2	0.800	1.000
A1	0.020	0.150
e	0.65(BSC)	
L	0.500	0.700
H	0.25(TYP)	
Θ	1°	7°

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